TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74HC280AP, TC74HC280AF

## 9 - BIT PARITY GENERATOR / CHECKER

The TC74HC280A is a high speed CMOS 9-BIT PARITY GENERATOR fabricated with silicon gate  $C^2MOS$  technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

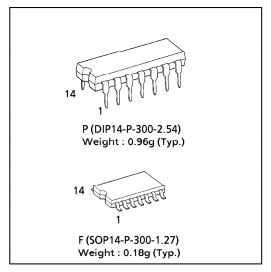
The TC74HC280A is composed of nine data inputs A thru I and odd/even parity outputs  $\Sigma$  ODD and  $\Sigma$  EVEN.

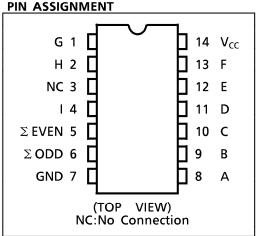
The odd parity output is high when an odd number of data inputs are high. The even parity output is high when an even number of data inputs are high.

The word-length capability is easily expanded by cascading. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### FEATURES:

- High Speed······ $t_{pd} = 22ns(typ.)$  at  $V_{CC} = 5V$
- Low Power Dissipation ············ $I_{CC} = 4\mu A(Max.)$  at Ta = 25°C
- High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Output Drive Capability ......10 LSTTL Loads
- Symmetrical Output Impedance… | I<sub>OH</sub> | = I<sub>OL</sub> = 4mA(Min.)
- Balanced Propagation Delays  $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range···· V<sub>CC</sub> (opr.) = 2V~6V
- Pin and Function Compatible with 74LS280

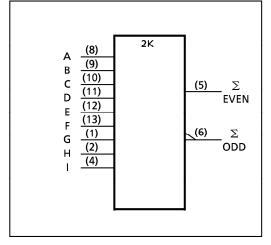




### TRUTH TABLE

Number of inputs A through I that are High	Outputs			
	Σ EVEN	ΣODD		
0, 2, 4, 6, 8	Н	L		
1, 3, 5, 7, 9	L	Н		

### **IEC LOGIC SYMBOL**



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## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	<b>−</b> 0.5~7	V
DC Input Voltage	V <sub>IN</sub>	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	<b>&gt;</b>
Input Diode Current	I <sub>IK</sub>	± 20	mA
Output Diode Current	lok	±20	mA
DC Output Current	I <sub>OUT</sub>	± 25	mΑ
DC V <sub>CC</sub> / Ground Current	I <sub>cc</sub>	± 50	mA
Power Dissipation	P <sub>D</sub>	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T <sub>stg</sub>	<b>−65~150</b>	°C

\*500mW in the range of Ta= $-40^{\circ}\text{C}\sim65^{\circ}\text{C}$ . From Ta= $65^{\circ}\text{C}$  to 85 °C a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  shall be applied until 300mW.

#### RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>cc</sub>	2~6	V
Input Voltage	VIN	0~V <sub>CC</sub>	V
Output Voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C
Input Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>	$0 \sim 1000 \text{ (V}_{CC} = 2.0\text{V)}$ $0 \sim 500 \text{ (V}_{CC} = 4.5\text{V)}$ $0 \sim 400 \text{ (V}_{CC} = 6.0\text{V)}$	ns

## DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL TEST CONDITION		NDITION	V <sub>cc</sub>	Ta = 25°C			Ta = -4	UNIT		
		INDITION	(V)	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT	
High - Level Input Voltage	V <sub>IH</sub>				1.50 3.15 4.20		_ 	1.50 3.15 4.20	_ _ _	>
Low - Level Input Voltage	VIL			2.0 4.5 6.0	_ _ _		0.50 1.35 1.80	_ _ _	0.50 1.35 1.80	>
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> =	$I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0		1.9 4.4 5.9		V
		$V_{IH}$ or $V_{IL}$	$I_{OH} = -4 \text{ mA}$ $I_{OH} = -5.2 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	_	4.13 5.63	_	
Low - Level $V_{OL}$ $V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 20 \mu A$	2.0 4.5 6.0	_ _ _	0.0 0.0 0.0	0.1 0.1 0.1	_ _ _	0.1 0.1 0.1	>		
		V <sub>IH</sub> Of V <sub>IL</sub>	$I_{OL} = 4$ mA $I_{OL} = 5.2$ mA	4.5 6.0	_	0.17 0.18	0.26 0.26	_	0.33 0.33	
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND		6.0	_	_	±0.1	_	± 1.0	_
Quiescent Supply Current	I <sub>CC</sub>	$V_{IN} = V_{CC}$ or GND		6.0	_		4.0	_	40.0	μA

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# AC ELECTRICAL CHARACTERISTICS ( $C_L = 15pF$ , $V_{CC} = 5V$ , $Ta = 25^{\circ}C$ , Input $t_r = t_f = 6ns$ )

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t <sub>TLH</sub> t <sub>THL</sub>		_	4	8	
Propagation Delay Time	t <sub>pLH</sub> t <sub>pHL</sub>		ı	22	35	ns

## AC ELECTRICAL CHARACTERISTICS ( $C_L = 50pF$ , Input $t_r = t_f = 6ns$ )

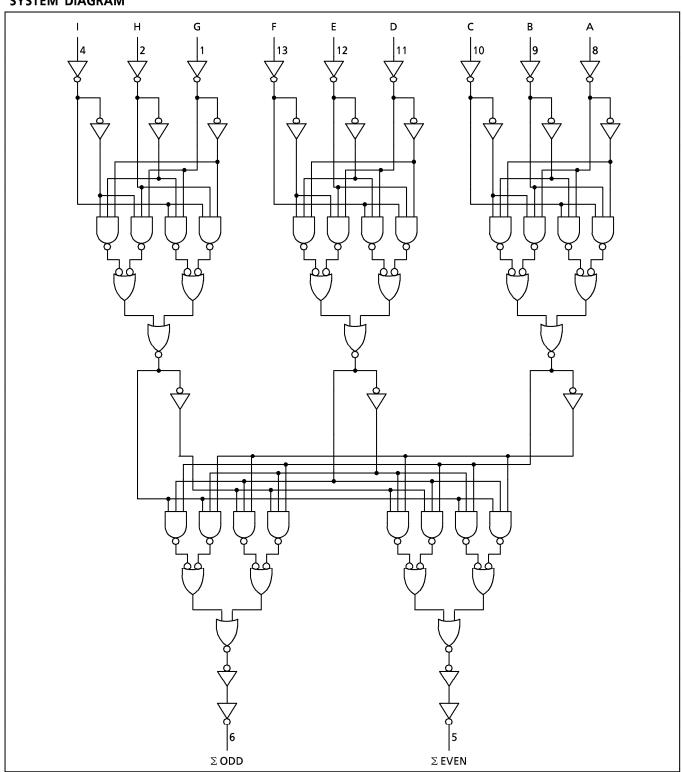
DADAMETED	CVARDOL	TEST CONDITION		Ta = 25°C			Ta = -4	LINUT	
PARAMETER SYMB	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Output Transition Time	t <sub>TLH</sub>		2.0	_	30	75	_	95	
	1 .		4.5	_	8	15	_	19	
	t <sub>THL</sub>		6.0	_	7	13	_	16	ا ۾ ا
Propagation Delay Time	<b> </b> +		2.0	_	80	200	-	250	ns
	t <sub>pLH</sub>		4.5	_	26	40	-	50	i i
	t <sub>pHL</sub>		6.0		22	34	_	43	
Input Capacitance	C <sub>IN</sub>			1	5	10	_	10	pF
Power Dissipation Capacitance	C <sub>PD</sub> (1)			_	61	_	_	_	рг

Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

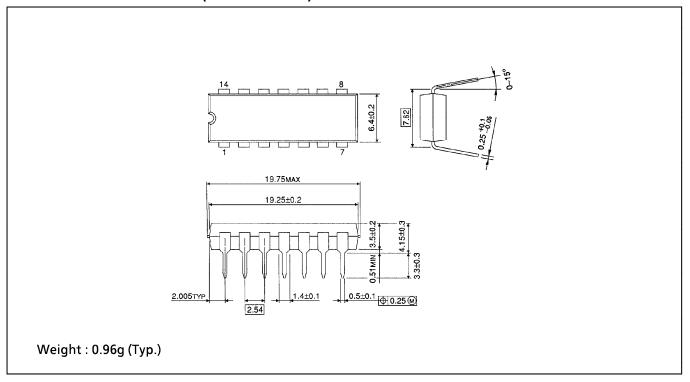
$$I_{CC}$$
 (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

# SYSTEM DIAGRAM



## DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



# SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm

